



GaN HEMT Pulsed Power Transistor  
3.1 - 3.5 GHz, 120W Peak, 300us Pulse, 10% Duty

Production V1  
02 Dec 11

## Features

- GaN depletion mode HEMT microwave transistor
- Common source configuration
- Broadband Class AB operation
- Thermally enhanced Cu/Mo/Cu package
- RoHS Compliant
- +50V Typical Operation
- MTTF of 114 years (Channel Temperature < 200°C)
- EAR99 Export Classification



## Application

## Product Description

The MAGX-003135-120L00 is a gold metalized matched Gallium Nitride (GaN) on Silicon Carbide RF power transistor optimized for civilian and military radar pulsed applications between 3100 - 3500 MHz. Using state of the art wafer fabrication processes, these high performance transistors provide high gain, efficiency, bandwidth, ruggedness over a wide bandwidth for today's demanding application needs. The MAGX-003135-120L00 is constructed using a thermally enhanced Cu/Mo/Cu flanged ceramic package which provides excellent thermal performance. High breakdown voltages allow for reliable and stable operation in extreme mismatched load conditions unparalleled with older semiconductor technologies.

## Typical Peak RF Performance

50V, 300us, 10%

50V, 100us, 10%

Freq. (MHz)	Pout (W Peak)	Pout (W Peak)	Pout (W Ave)	Gain (dB)	RL (dB)	Eff (%)
3100	10	134.3	13.4	11.3	-7	50.3
3300	10	138.6	13.8	11.4	-9	50.3
3500	10	134.1	13.4	11.2	-12	49.5

Freq. (MHz)	Pout (W Peak)	Pout (W Peak)	Pout (W Ave)	Gain (dB)	RL (dB)	Eff (%)
3100	10	142	14.2	11.5	-7	52.0
3300	10	145	14.5	11.6	-9	51.6
3500	10	140	14.0	11.5	-12	50.2

Typical RF performance measured in M/A-COM RF test fixture. Devices tested in common source Class-AB configuration as follows:  
Vdd=50V, Idq=300mA (pulsed gate bias), F=3.1 - 3.5 GHz, Pulse Width=300us, Duty=10%.

## Ordering Information

MAGX-003135-120L00  
MAGX-003135-SB5PPR

120W GaN Power Transistor  
Evaluation Fixture

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### Absolute Maximum Ratings Table (1, 2, 3)

Supply Voltage (Vdd)	+65V
Supply Voltage (Vgg)	-8 to 0V
Supply Current (Id1)	6700 mA
Input Power (Pin)	+36 dBm
Absolute Max. Junction/Channel Temp	200 °C
MTTF (T <sub>J</sub> <200°C)	114 years
Pulsed Power Dissipation (Pavg) at 85 °C	170 W (100us)
	144 W (300us)
Thermal Resistance, (T <sub>channel</sub> = 200 °C) V <sub>DD</sub> = 50V, I <sub>DQ</sub> = 300mA, Pin = 10Wpk, Pulse Width 100uS, Duty 10%	0.5 °C/W
Thermal Resistance, (T <sub>channel</sub> = 200 °C) V <sub>DD</sub> = 50V, I <sub>DQ</sub> = 300mA, Pin = 10Wpk, Pulse width 300uS, Duty 10%	0.8 °C/W
Operating Temp	-40 to +95C
Storage Temp	-65 to +150C
Mounting Temperature	See solder reflow profile
ESD Min. - Machine Model (MM)	50 V
ESD Min. - Human Body Model (HBM)	>250 V
MSL Level	MSL1

(1) Operation of this device above any one of these parameters may cause permanent damage.

(2) Channel temperature directly affects a device's MTTF. Channel temperature should be kept as low as possible to maximize lifetime.

(3) For saturated performance it recommended that the sum of (3\*Vdd + abs(Vgg)) <175

Parameter	Test Conditions	Symbol	Min	Typ	Max	Units
<b>DC CHARACTERISTICS</b>						
Drain-Source Leakage Current	V <sub>GS</sub> = -8V, V <sub>DS</sub> = 175V	I <sub>DS</sub>	-	0.5	9	mA
Gate Threshold Voltage	V <sub>DS</sub> = 5V, I <sub>D</sub> = 23mA	V <sub>GS(th)</sub>	-5	-3	-2	V
Forward Transconductance	V <sub>DS</sub> = 5V, I <sub>D</sub> = 9A	G <sub>M</sub>	3.3	-	-	S
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	Not applicable - Input internally matched	C <sub>GS</sub>	N/A	N/A	N/A	pF
Output Capacitance	V <sub>DS</sub> = 50V, V <sub>GS</sub> = -8V, F = 1MHz	C <sub>OSS</sub>	-	13.4	16	pF
Reverse Transfer Capacitance	V <sub>DS</sub> = 50V, V <sub>GS</sub> = -8V, F = 1MHz	C <sub>RSS</sub>	-	1.4	2.2	pF

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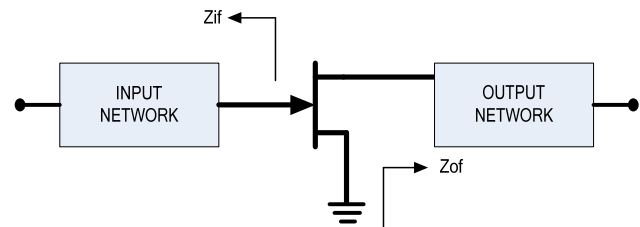
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**Electrical Specifications:  $T_C = 25 \pm 5^\circ\text{C}$  (Room Ambient )**

Parameter	Test Conditions	Symbol	Min	Typ	Max	Units
<b>RF FUNCTIONAL TESTS (<math>V_{DD} = 50\text{V}</math>, <math>I_{DQ} = 300\text{mA}</math>, 300us pulse / 10% duty, 3.1 - 3.5 GHz)</b>						
Output Power	Pin = 10W Peak, 1W Ave	$P_{OUT}$	120 12	135 13.5	-	W Peak W Ave
Power Gain	Pin = 10W Peak, 1W Ave	$G_P$	10.8	11.8	-	dB
Drain Efficiency	Pin = 10W Peak, 1W Ave	$\eta_D$	45	52	-	%
Load Mismatch Stability	Pin = 10W Peak, 1W Ave	VSWR-S	5:1	-		-
Load Mismatch Tolerance	Pin = 10W Peak, 1W Ave	VSWR-T	10:1	-		-

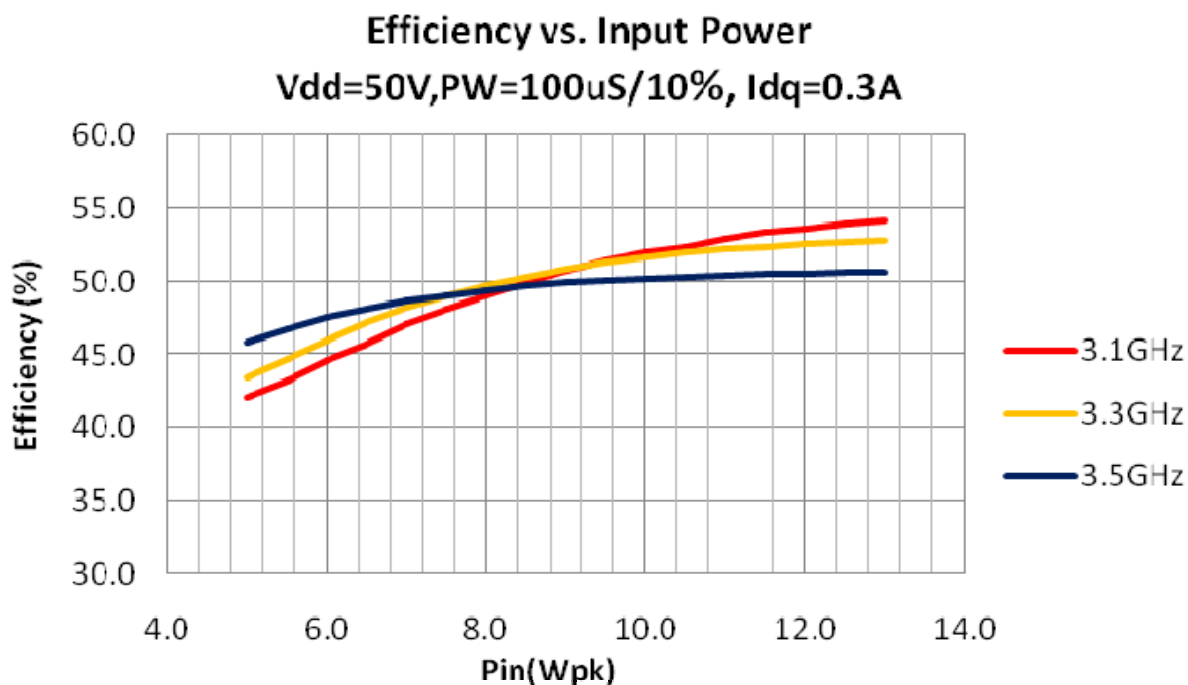
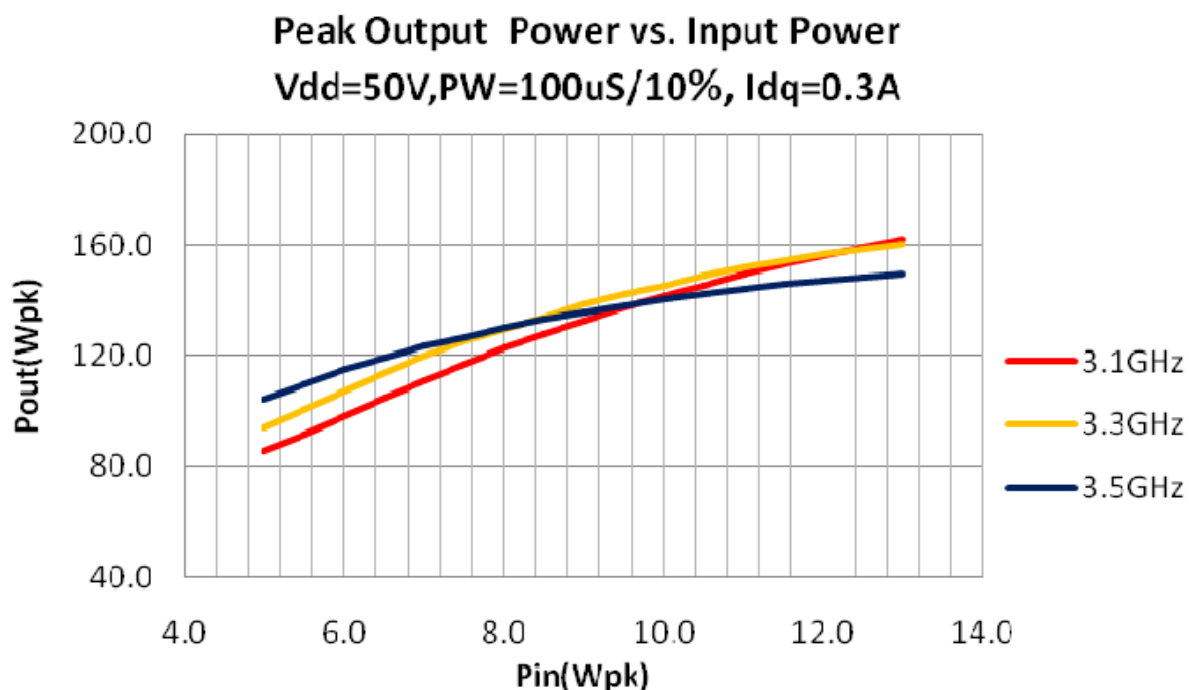
### Test Fixture Impedance

F (MHz)	$Z_{IF} (\Omega)$	$Z_{OF} (\Omega)$
3100	$5.9 - j4.2$	$4.1 - j2.4$
3300	$5.2 - j4.8$	$4.0 - j2.8$
3500	$3.9 - j5.0$	$2.6 - j2.6$



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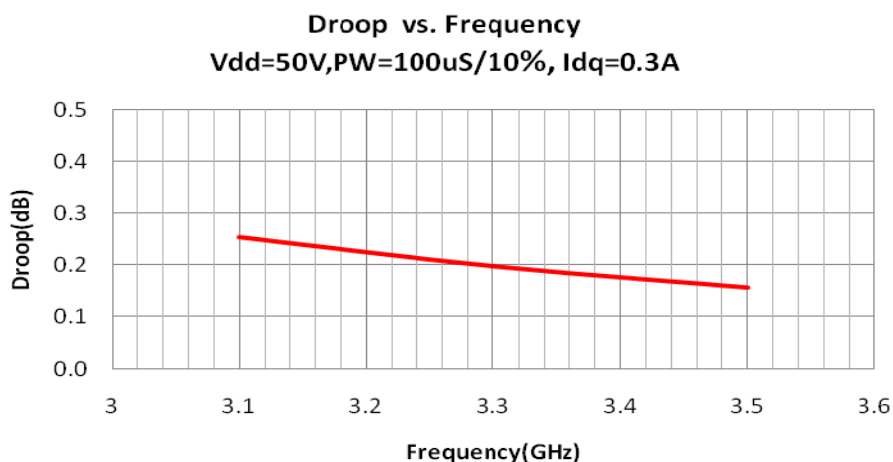
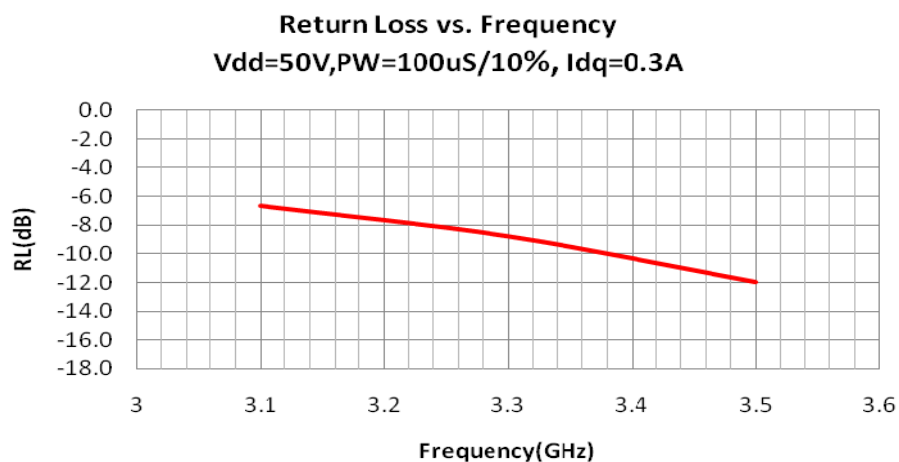
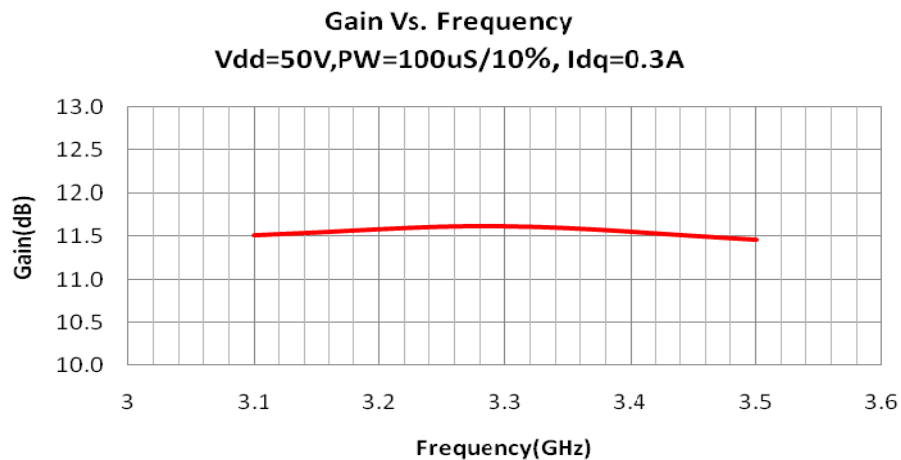
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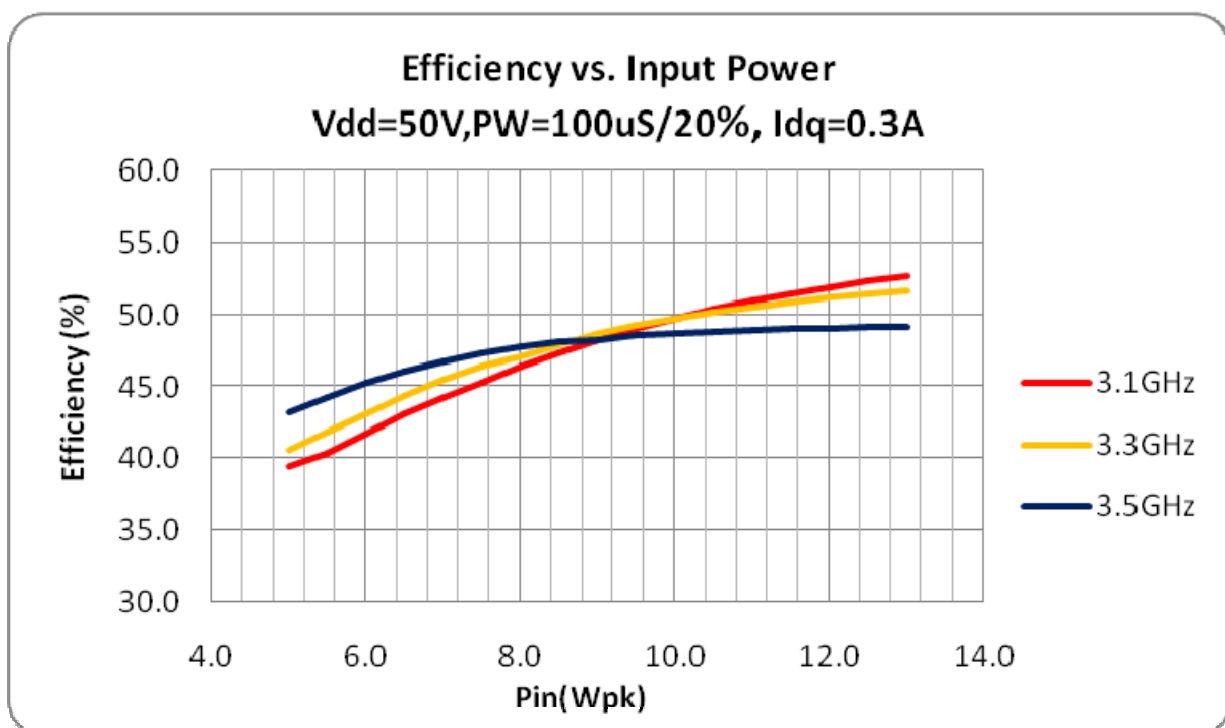
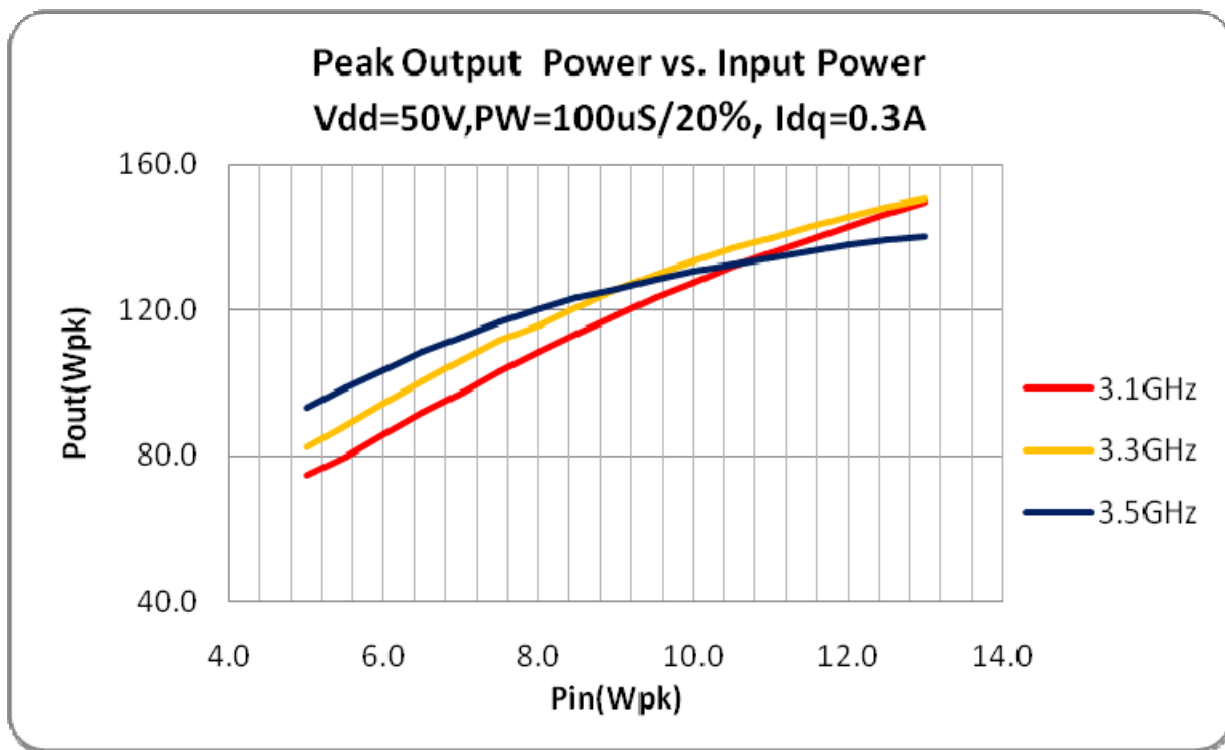
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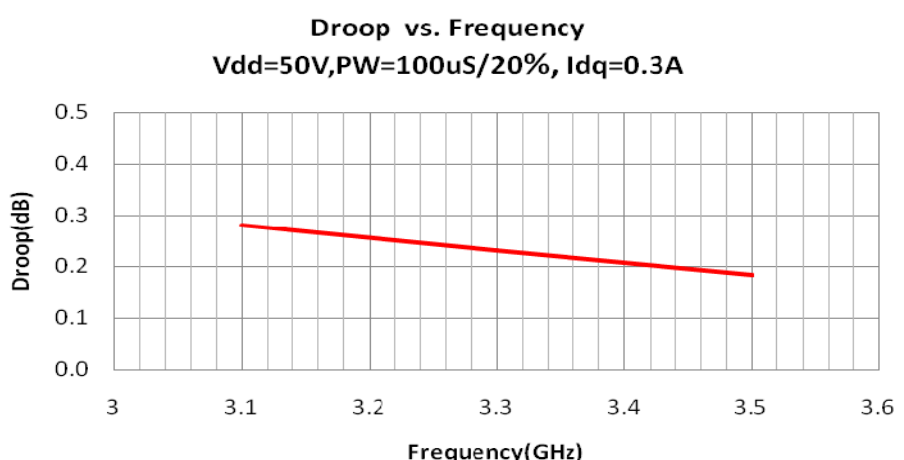
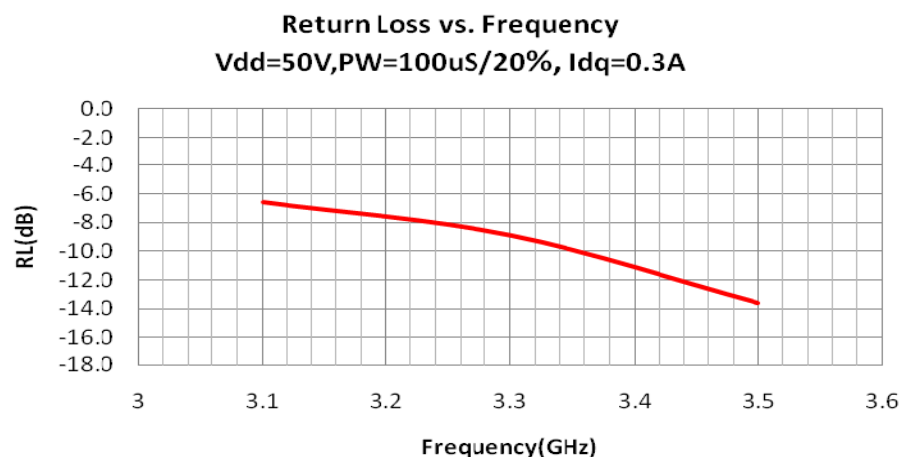
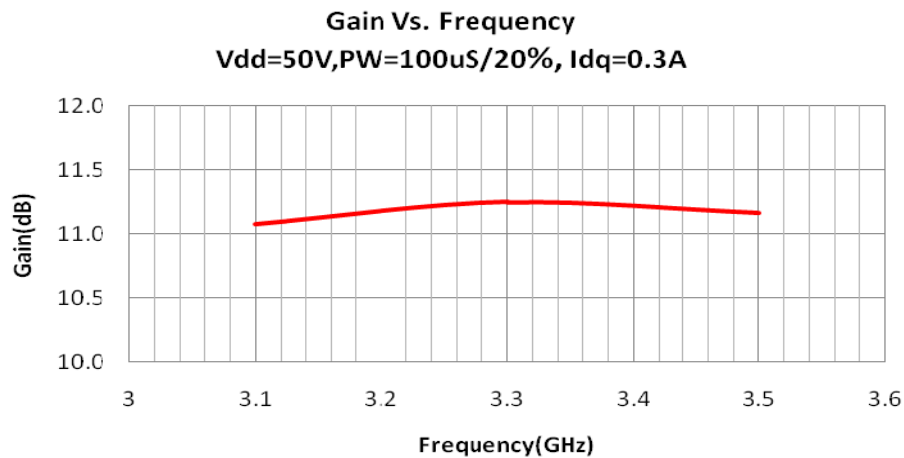
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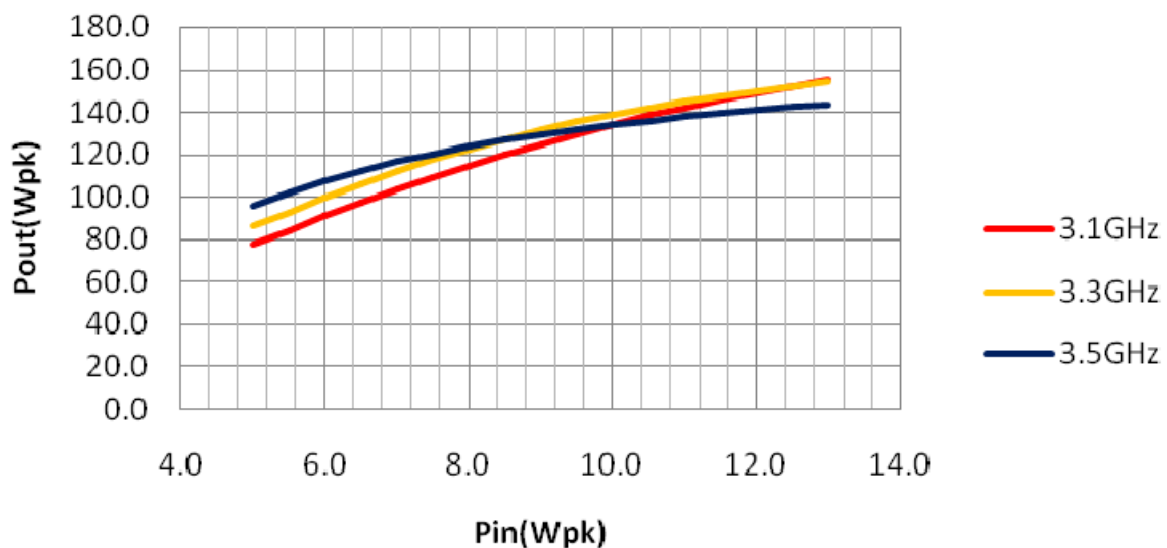
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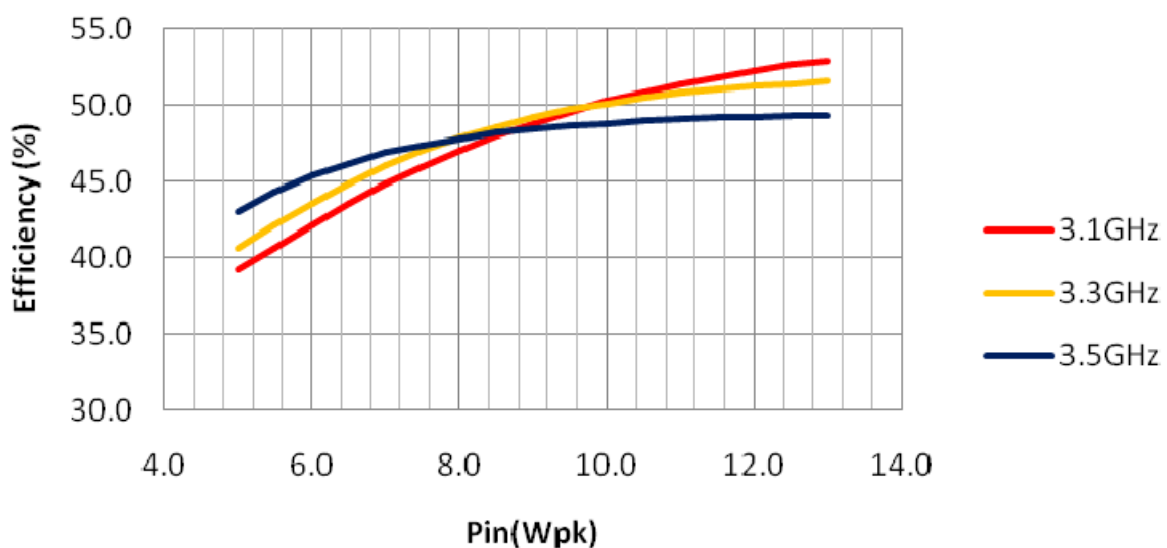
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**Peak Output Power vs. Input Power**  
**Vdd=50V, PW=300uS/10%, Idq=0.3A**

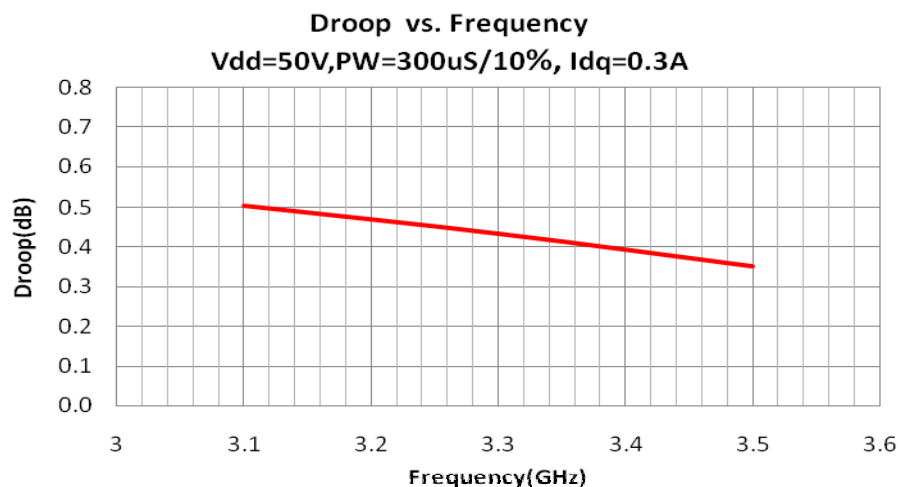
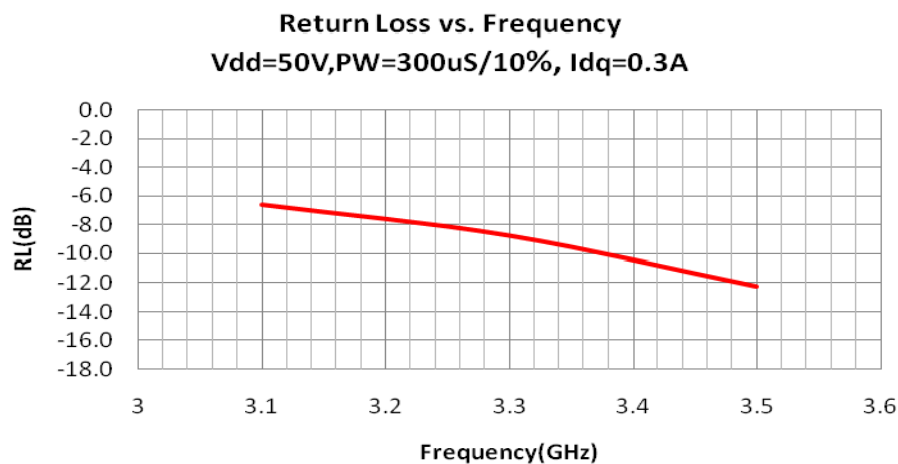
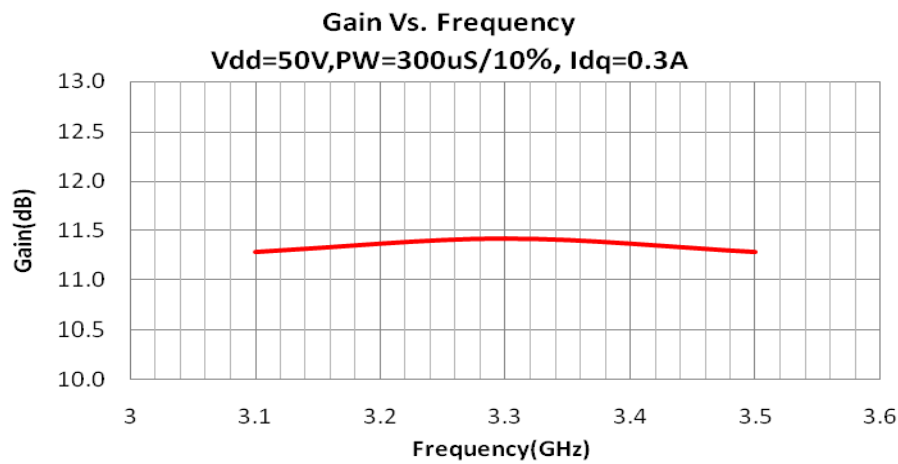


**Efficiency vs. Input Power**  
**Vdd=50V, PW=300uS/10%, Idq=0.3A**



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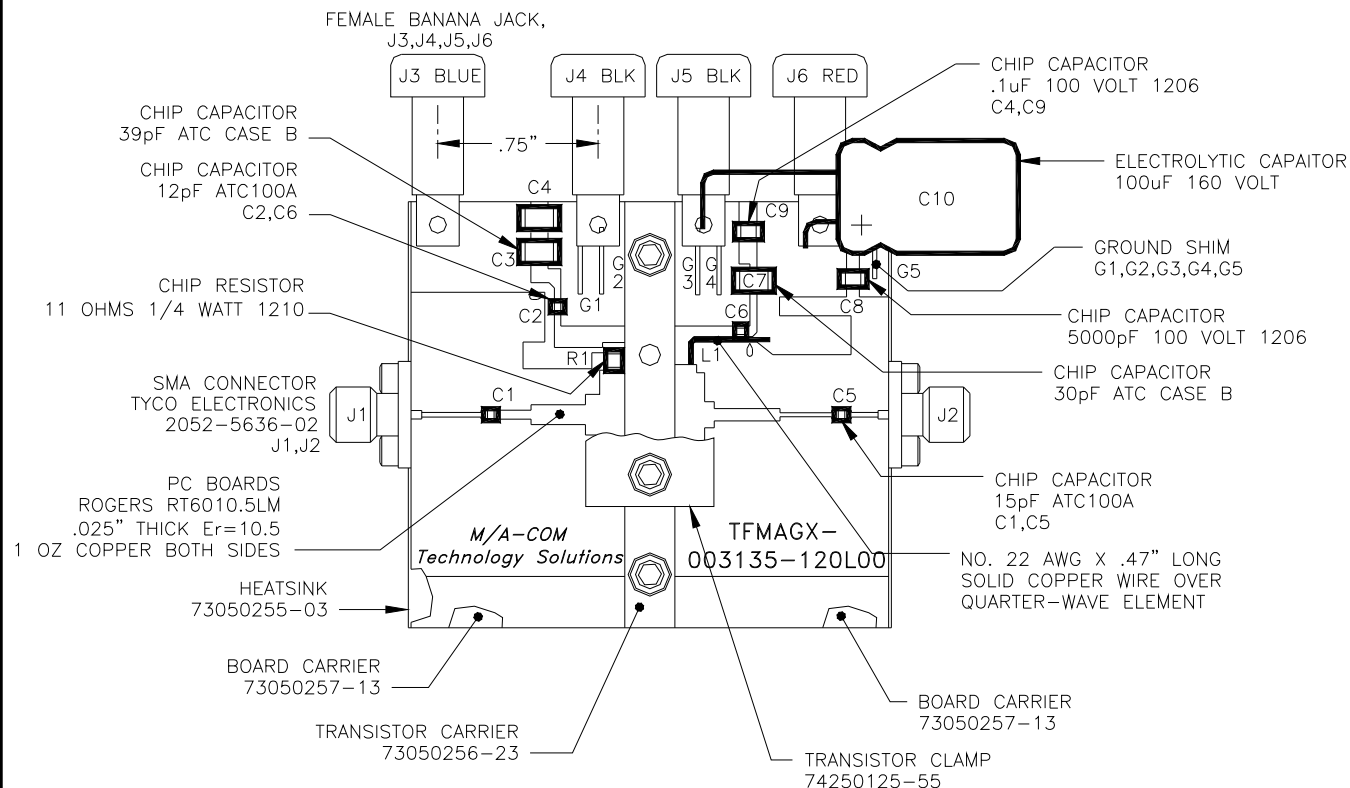
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## Test Fixture Assembly

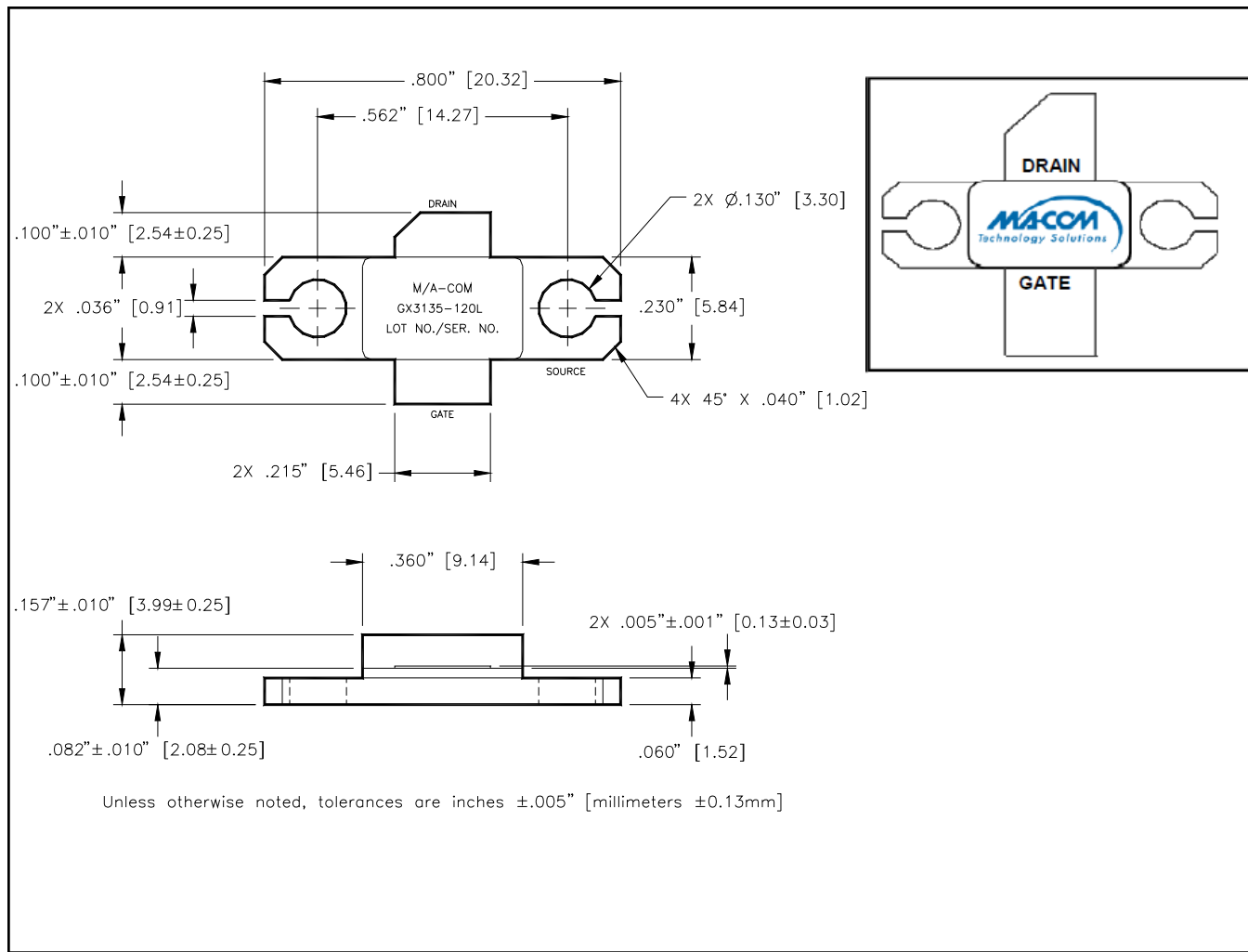


ASSEMBLY VIEW

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## Outline Drawing



## CORRECT DEVICE SEQUENCING

### TURNING THE DEVICE ON

1. Set  $V_{GS}$  to the pinch-off ( $V_P$ ), typically -5V
2. Turn on  $V_{DS}$  to nominal voltage (60V)
3. Increase  $V_{GS}$  until the  $I_{DS}$  current is reached
4. Apply RF power to desired level

### TURNING THE DEVICE OFF

1. Turn the RF power off
2. Decrease  $V_{GS}$  down to  $V_P$
3. Decrease  $V_{DS}$  down to 0V
4. Turn off  $V_{GS}$

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